

Silicon PNP Power Transistors

2SA738

DESCRIPTION

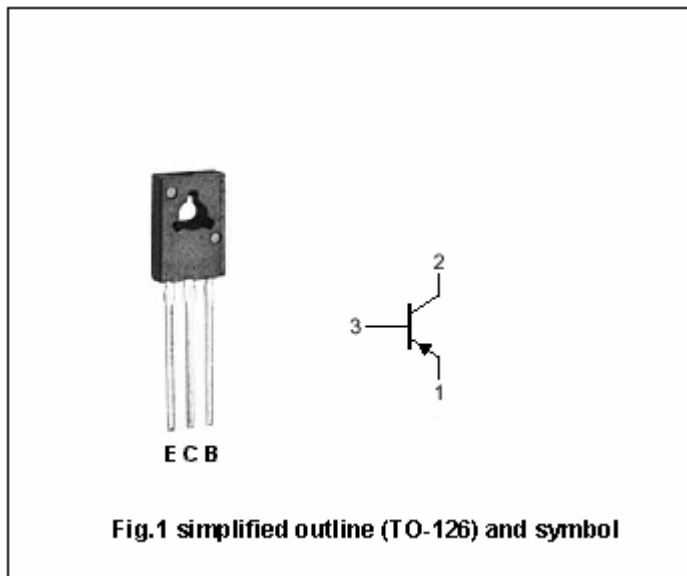
- With TO-126 package
- High current
- Complement to type 2SC1368

APPLICATIONS

- Driver stages in high-fidelity amplifiers and television circuits

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |



Absolute maximum ratings (Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|---------------------------|----------------|---------|------|
| V_{CBO} | Collector-base voltage | Open emitter | -25 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -25 | V |
| V_{EBO} | Emitter -base voltage | Open collector | -5 | V |
| I_C | Collector current | | -1.5 | A |
| I_{CM} | Collector current-Peak | | -2.0 | A |
| P_t | Total power dissipation | $T_C=25$ | 8 | W |
| T_j | Junction temperature | | 150 | |
| T_{stg} | Storage temperature | | -65~150 | |

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CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-10mA; I _B =0 | -25 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-0.5A; I _B =-50mA | | | -0.5 | V |
| V _{BE} | Base-emitter voltage | I _C =-500mA ; V _{CE} =-2V | | | -1.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-25V; I _E =0 | | | -1.0 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -1.0 | μ A |
| h _{FE-1} | DC current gain | I _C =-150mA ; V _{CE} =-2V | 35 | | 320 | |
| h _{FE-2} | DC current gain | I _C =-500mA ; V _{CE} =-2V | 25 | | | |
| f _T | Transition frequency | I _C =-50mA; V _{CE} =-5V | | 160 | | MHz |

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PACKAGE OUTLINE

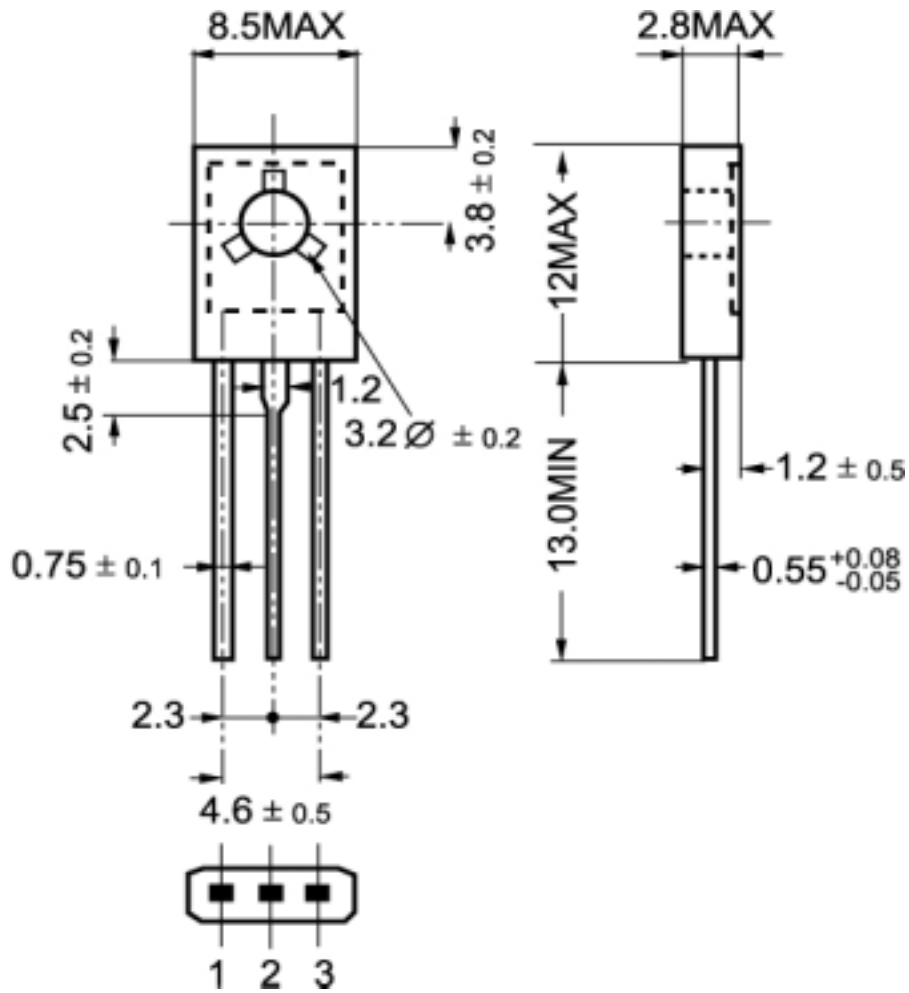


Fig.2 Outline dimensions